In the Specification

Please amend the specification as follows. No new matter is added.

Please amend paragraph 0018 as follows:

[0018]   The formed crystal is preferably kept at a temperature close to the melting temperature by ~~at least one of shielding the crystal material pulled out of the melt and solidified, from heat-radiation and conductivity loses and~~ at least partly offsetting heat loses by additional heating. [[.]] <u>More particularly,</u> the ~~The~~ process for growing single crystals <u>is a process</u> wherein crystal material is melted in a crucible and a crystal nucleus is immersed in the molten crystal material and slowly pulled out, wherein the crystal formed during the pulling is kept at a temperature close to <u>and above a</u> melting temperature of the output material <u>by induction heating of an electrically conductive susceptor including at least one electrically conductive tube surrounding and heating the crucible, at least while the crystal is slowly pulled out, and surrounding and maintaining a temperature gradient in the pulled crystal within 4 degrees K per cm.</u> The invention further includes a device for growing single crystals having a crucible to receive molten crystal material, a heating device for heating the crucible and the crystal material and a device for pulling the crystal out of the melt using an immersed crystal nucleus wherein ~~at least one of a shield and~~ <u>a</u> heating element is provided surrounding the crystal during the pulling, which prevents rapid cooling of the solidified crystal material in comparison with the melt and a large temperature gradient within solidified crystal material. <u>The heating device and heating element include an electrically conductive susceptor having at least one electrically conductive</u>

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tube surrounding and heating the the crucible and an inductor is provided for inductively heating

the susceptor.

Please amend paragraph [0026] as follows:

[0026] As seen in Figure 1, in ~~In~~ one advantageous version of the process according to the

invention the small temperature gradient is achieved in that the crucible 14, at least during the

slow pulling-out stage, is arranged in a preferably vertically arranged tube 22 made from

electrically conductive material, which serves as a susceptor, and the tube 22 in inductively

heated with an inductor 24.

Please amend paragraph [0035] as follows:

[0035] As seen in figure 1, ~~With~~ with respect to the device , the object described at the start is

acheived by a device 10 for growing single crystals 12 with a crucible 14 to receive molten

crystal material 16, a heating device 18 for heating the crucible 14 and/or crystal material 16 and

a device 20 for pulling crystals 12 out of the melt, for example using an immersed crystal

nucleus, characterized in that a shield and/or heating element 18 surrounding the crystal during

the pulling is provided, which prevents rapid cooling of the solidified crystal material compared

with the melt 16 and/or a large temperature gradient within the solidified crystal material 12.

Please amend paragraph [0036] as follows:

[0036] The heating device 18 advantageously consists of a tube 22 made from electrically

conductive material (susceptor) preferably arranged vertically, inside which the crucible 14 is

arranged, and an inductor 24, which heats the tube 22 inductively. The inductive construction

has the advantage that no electrical connections have to be introduced into the furnace. It is

understood that even if the construction of the susceptor as a single-piece tube is particularly

preferable, the susceptor can of course also be made up of two or more pieces standing on one

another, or in another manner.

After paragraph **[0018]**, please insert a new section as follows:

Brief Description of the Drawings

Figure 1 shows a cross sectional view of a device in accordance with the invention

suitable for practicing the process of the invention.